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List of Contents, Volume 50, 1995

Progress in our understanding of Structure Bonding and Reactivity of Metal Surface and Absorbed Monolayers At The Molecular Level: A 25 Year Perspective
by G. A. SOMORJAI 1

The Amazing Story of Semiconductor Surface Structures
by C. B. DUKE 31

Surface and Interface Analysis At 3rd Generation light Sources
by F. J. HIMPLE, H AKATSU, J.A. CARLISLE, D.G.J. SUTHERLAND I. JIMENEZ, L. J.TERMINELLO, J. J. JIA, T. A. CALLCOTT, M. G. SAMANT, J STÖHR, D. L. EDERER, R.C.C. PERERA, W. TONG, D. K. SHUNH. 37

Electromagnetic Interactions with Rough Metals Surfaces
by F. J. GARCIA-VIDAL and J. B. PENDRY 55

Tamm Surface States in Semiconductor Superlattices
by M. STĘŚLICKA 65

Metal-Oxide Surfaces
by V.E. HENRICH 77

Edge Of Two-Dimensional Electron Systems under Strong Magnetic
by I. BARTOS and B. ROSENSTEIN 91

Weak Interactions Between Deposited Metal Overlayers and Organic Funcional Groups of Self-Assembled Monolayers
by G.C. HERDT, D.R. JUNG and A.W. CZANDERNA 103

Photochemical Desorption From Chlorinated Si (100) and Si (111) Surfaces Mechanisms and Models
by T. RHODIN 131

Theory of Image States at Magnetic Surface at Magnectic Surfaces
by M. NEKOVEE and J. E. INGLESFIELD 149

Growth Modes of Ultrathin Metal Films on Dissimilar Metal Substrates
by A. J. SLAVIN 159

Water At Surfaces: What can we Learn from Vibrational Spectroscopy?
by F. BENSEBAA and T. H. ELLIS 173

Rough Silver Films Studied by Surface Enhanced Raman Spectroscopy and Low Temperature Scanning Tunnelling Microscopy
by C. DOUKETIS, T. L. HASLETT, Z WANG, M. MOSKOVITS and S. IANNOTA 187

Electron Energy Loss Studies of Room Temperatute Co Adsorption On 197

Cu (100) Induced by Elctron or Ion Irradiation
by H. YU, D.Q.HU and K. T. LEUNG

Theory of the Vibration Line Shape of an Adatom at a Bridge Site 217
by R. Tu. and P. Piercy.

Effect of Anion Adsorption on Early Stages of Copper Electrocrystallization 227
at Au (111) Surface
by S. Wu, J. Lipkowski, T. Tyliszczak, and A. P. Hitchcock

Adsorption of Insoluble Surfactants at the Au (111) / Solution Interface 237
by D. BIZZOTTO and J. LOPKOWSKI

What Determines the Structures Formed by Oxygen at Low Index Surfaces 247
of Copper?
By W. LIU, K. C. WONG, H. C. ZENG and K. A. R. MITCHELL

Optimization of Zinc Phosphate Coating on 7075-T6 Aluminum Alloy 259
by J. F. YING, B. J. FLINN, M. Y. ZHOU, P. C. WONG, K. A. R MITCHELL
and T. FOSTER

Examination of Clinical Surface Preparations on Titanium and Ti6A14V by 269
X-ray Photoelectron Spectroscopy and Nuclear Reaction Analysis
by B. W. CALLEN, R. N. S. SODHI and K. GRIFFITHS

Chemical Etching of Silicon: Smooth, Rough, and Glowing Surfaces 283
by L. A. JONES, G. M. TAYLOR, F.-X. WEI and D. F. THOMAS

Confocal Imaging of Porous Silicon with a Scanning Laser 295
Macroscope/Microscope
by A. C. RIBES, S. DAMASKINOS, A. E. DIXON, K. A. ELLIS,
S. P. DUTTAGUPTA and P. M. FAUCHET

Influence of HF Treatment of Si on Surface Electron Kinetics 305
by S. GRABTCHAK and M. COCIVERA

Indentification of the Adsorption Sites of Molecular Oxygen on Si (111)
using XPS 315
B. LAMONTAGNE, D. ROY, R. SPORKEN and R. CAUDANO

Structural and Electronic Properties of Sulfur Passivated Inp (100) 325
by C. E. J. MITCHELL, I. G. HILL, A. B. McLEAN and Z. H. LU

XANES Studies of III-V Semiconductor Surface Passivation 335
by Z. H. LU

Study of In-Situ Surface Cleaning for Si and SiGe Epitaxy on Si with
a Novel Ion Beam Vapor/Assisted Deposition Technique 347
by S. MOHAJERZADEH, C. R. SELVAKUMAR, D. E. BRODIE,

M. D. ROBERTSON, and J. M. CORBETT

Surface Charge Spectrocopy and its Applications 357
by R. W. M. KWOK and W. M. LAU

Characterization of Elastic Strains In Semiconductor Heteroepitaxial Layers by HREM 377
by M. D. ROBERTSON, J. M. CORBETT and J. B. WEBB

On the Multiple Peaks in Charge-Transfer Probability Versus Laser Frequency in the Theory of Laser Assisted Surface Ion Neutralization 389
by F. O. GOODMAN and H. NAKAMURA

Adhesion to Mineralized Tissue Bonding to Human Dentin 407
by M. DiRENZO, T. H. ELLIS, E. SACHER and I. STANGEL

PROGRESS IN SURFACE SCIENCE

AUTHOR INDEX

Akatsu, H. 37
Bartos, I. 91
Bensebaa, F. 173
Callcott, T. A. 37
Carlisle, J. A. 37
Czanderna, A. W. 103
Douketis, C. 187
Duke, C. B. 31
Ederer, D. L. 37
Ellis, T. H. 173
Flinn, B. J. 259
Foster, T. 259
Garcia-Vidal, F. J. 55
Haslett, T. L. 187
Henrich, V. E. 77
Herdt, G. C. 103
Himpsel, F. J. 37
Hitchcock, A. P. 227
Hu, D. Q. 197
Iannotta, S. 187
Inglesfield, J. E. 149
Jia, J. J. 37
Jimenez, I. 37
Jung, D. R. 103
Leung, K. T. 197
Lipkowski, J. 227
Liu, W. 247
Mitchell, K. A. R. 259 , 247
Moskovits, M. 187
Nekovee, M. 149
Pendry, J. B. 55
Perera, R. C. C. 37
Piercy, P. 217
Rhodin, T. 131
Rosenstein, B. 91
Rowntree, P. A. 207
Samant, M. G. 37
Shunh, D. K. 37
Slavin, A. J. 159
Somorjai, G. A. 3
Stęślicka, M. 65
Stöhr, J. 37
Sutherland, D. G. J. 37
Terminello, L. J. 37
Tong, W. 37
Truong, K. D. 207
Tu, R. 217
Tyliszczak, T. 227
Wang, Z. 187
Wong, K. C. 247
Wong, P. C. 259
Wu, S. 227
Ying, J. F. 259
Yu, H. 197
Zeng, H. C. 247
Zhou, M. Y. 259

PROGRESS IN SURFACE SCIENCE

SUBJECT INDEX

7075-T6 aluminum alloy, zinc phosphate coating 259–267
Adatom, vibrational line shape 217–225
Adsorbate, mobility 23–27
Adsorbate-induced restructuring 16–20
  coverage dependence 17–20
  dynamics 24–25
Adsorption
  12-(9-anthroyloxy) stearic acid 243–245
  anion 227–236
  CO on Cu(100) 197–205
  octadecanol 239–242
  oxygen on silicon(111) 315–324
Advanced method of transient microwave photoconductivity (AMTMP) 305–313
Alkanethiols, monolayers on gold 108–109
Alloys
  growth 161–163
  stoichiometry 166–167
7075-T6 Aluminum alloy 259–267
AMTMP. *See* advanced method of transient microwave photoconductivity
Anion adsorption, copper electrocrystallization 227–236
12-(9-anthroyloxy) stearic acid (12-AS) 243–245
AS-t. *See* Auger signal-time
Auger signal-time (AS-t) 160–166

Binding energy 40
  oxygen adsorption 315–324
Bridge sites, adatoms 217–225
Butanethiol, monolayers on gold 207–216

C_4 sub-monolayers 210–212
  dynamical behaviour 211–212
  steady-state behaviour 211
C_4SAMs 212–215
Cadmium Selenium, electron kinetics 309
Carbon monoxide adsorption, EELS 197–205
Carbon monoxide coadsorption 23–24
Carbon monoxide/ethylidyne coadsorption 9–10
Charge transfer probability, multiple peaks 389–405
Charge traps, SCS 364–369
Chemical etching, silicon 283–293
Chloride ion, copper electrocrystallization 229–233
Chlorinated Si surfaces, photochemical desorption 131–146
Chlorine passivated GaAs(111) 341–343
Coadsorbate-induced compression 23–24
Coadsorption 9–10, 20–24
Compression, coadsorbate-induced 23–24
Confocal imaging, porous silicon 295–304
Copper
  CO adsorption on 197–205
  electrocrystallization 227–236
  surfaces, oxygen structures 247–257
Copper/CN 109–110, 116–119
Copper/OH 109–110, 119–121
Core levels 40
Cumulative sum of deviations (CUSUM), elastic strains 377–386
CUSUM. *See* Cumulative sum of deviations

Dangling bonds (DBs), passivation 335–345
DBs. *See* Dangling bonds
Dentin 407–418
  adhesion to apatite 409–410
  adhesion to protein 410–411
  chemical reactions 414–417
  components 408–409
  surface analytical techniques 411–414
Desorption, photochemical 131–146

EELS. *See* Electron energy loss spectroscopy
Elastic strains, heteroepitaxial semiconductor systems 377–386
Electromagnetic interactions, rough metal surfaces 55–64

Electron energy loss spectroscopy (EELS) 161–162
  CO adsorption 197–205
Electron irradiation, CO on Cu(100) 147–205
Electron kinetics, HF treatment of Si 305–313
Electron structure 92–95
Energy, superlattice surface states 68–69
Etching
  chlorinated Si surfaces 131–146
  silicon 283–293
Ethylidyne/CO coadsorption 9–10

Gallium arsenide, electron kinetics 309
Gallium arsenide(111), Cl passivation 341–343
Gallium arsenide/$Al_xGa_{1-x}As$ superlattice, energy spectrum 66–67, 70–74
Gold
  alkanethiol monolayers 108–109
  butanethiol monolayers 207–216
Gold(111)
  copper electrocrystallization 227–236
  insoluble surfactants adsorption 237–246
Growth modes, metal films 159–172

Hall conductivity, quantum wires 95–100
HEMA. *See* Hydroxyethyl methacrylate
High resolution electron microscopy (HREM), heteroepitaxial semiconductor systems 377–386
High-resolution electron energy loss spectroscopy (HREELS), water at surfaces 173–185
HREELS. *See* High-resolution electron energy loss spectroscopy
HREM. *See* High resolution electron microscopy
Hydrogen fluoride treatment, silicon 305–313
2-Hydroxyethyl methacrylate (HEMA) 414–417

IBVD. *See* Ion beam vapor deposition
Ice Ih, low-temperature 14–15
IHQE. *See* Integer quantum Hall effect
Image resonance 154–157
Image states
  computational methods 150–151
  magnetic surfaces 149–158
  spin splitting 151–154
In situ surface cleaning 347–356
Indium phosphide(100), sulfur passivated 325–334, 337–341
Infrared reflection absorption spectroscopy 209
Infrared spectroscopy, butanethiol monolayers on gold 207–216
Insoluble surfactants, adsorption 237–246
Insulator/semiconductor structure, SCS 357–376
Integer quantum Hall effect (IHQE) 95–100
Intensity-versus-energy curves, oxygen/copper surfaces 249–251
Interface traps, SCS 359–363
Interfaces
  bonding 43–46
  electronic structures 43–46
Ion Beam Vapor Deposition (IBVD) 347–356
Ion irradiation, CO on Cu(100) 147–205
Ion scattering spectroscopy (ISS)
  compositional death profiles 121–126
  SAMs 111–112
Iron(110), spin splitting 151–154
ISS. *See* Ion scattering spectroscopy

Kinetic models, silicon etching 291–292
Kinetics 305–313
Kronig-Penney-type model 66–67

Laser frequency, LASIN 389–405
Laser-Assisted Surface Ion Neutralization (LASIN) 389–405
LASIN. *See* Laser-Assisted Surface Ion Neutralization
Lattice-fringe spacings, heteroepitaxial layers 377–386
LEED. *See* Low-energy electron diffraction

Light in Complex Structures, Theory of 57–60
Light sources, 3rd generation 37–51

Low-energy electron diffraction (LEED)
See also tensor LEED analyses
magnetite Fe_3O_4 (111) 12–14
metal-oxides 79–80
Scanning Tunneling Microscopy 6–9
sulfur passivated InP(100) 327–329
vibrational spectroscopy 9–10

MACROscope-Microscope 295–304
Magnetic fields, two-dimensional electron systems 91–101
Magnetic multilayers, quantum effects 47–50
Magnetic surfaces, image states 149–158
Magnetite Fe_3O_4 (111), LEED crystallography 12–14
Metal films, growth modes 159–172
Metal overlayers, organic group interactions 103–129
Metal surfaces
electromagnetic interactions 55–64
reactivity 3–29
Metal-oxides
gas/surface interactions 86–89
LEED 79–80
non-transition 82–83
surface electronic structure 81–85
surface geometry 79–81
surfaces 77–90
Mineralized tissue, human dentin bonding 407–418

Nitric acid passivation, surface preparation 269–279
NRA. *See* Nuclear reaction analysis
Nuclear reaction analysis (NRA)
Ti6A14V surface preparation 269–279
Ti surface preparation 269–279

Octadecanol, adsorption 239–242
Organic functional group, metal overlayer interactions 103–129

Oxygen
adsorption on to silicon(111) 315–324
copper surfaces 247–257

Passivation
sulfur passivated InP(100) 325–334
XANES studies 335–345
Penetration, metal/organic functional groups 109–110, 112–114
Peroxy radical, oxygen adsorption 315–324
pH level, zinc phosphate coating process 265–266
Photochemical desorption, chlorinated silicon surfaces 131–146
Pressure effects, photochemical desorption 139

Quantum effects, magnetic multilayers 47–50
Quantum wires, Hall conductivity 95–100

RAIRS. *See* Reflection-absorption infrared spectroscopy
Reactivity
metal surfaces 3–29
metal/organic functional groups 112–114
Reconstruction
clean metal surfaces 11–12
oxide surfaces 12–14
semiconductor surfaces 11–12
Reflection-absorption infrared spectroscopy (RAIRS), water at surfaces 173–185
Relaxation
clean metal surfaces 11–12
oxide surfaces 12–14
semiconductor surfaces 11–12
Restructuring, adsorbate-induced 16–20, 24–25
Rhenium/sulfur
coadsorbate-induced compression 23
structures 5–8

SAMs. *See* Self-assembled monolayers

Scanning electron microscope, zinc phosphate coating process 259–267
Scanning Force Microscope (SFM), silicon etching 283–293
Scanning laser MACROscope-Microscope 295–304
Scanning tunneling microscopy (STM)
  Low-Energy Electron Diffraction 6–9
  silver films 187–195
  TiO_2(110) 80–81
SCS. *See* Surface charge spectroscopy
Secondary ion mass spectrometry (SIMS), zinc phosphate coating process 259–267
Self-assembled monolayers (SAMs) 105–129
  preparation 110
Semiconductors
  bonding of interfaces 43–47
  electronic structure of interfaces 43–47
  heteroepitaxial layers 377–386
  III-IV, surface passivation 335–345
  in situ surface cleaning 347–356
  passivation, XANES studies 335–345
  scaling and universality 35
  sulfur passivated InP(100) 325–334
  superlattices, Tamm surfaces states 65–76
  Surface Charge Spectroscopy 357–376
  surface chemistry 41–42
  surface reconstruction 11–12, 33–35
  surface relaxation 11–12
  surface structure 31–36
  surface structure motifs 33
SERS. *See* Surface enhanced Raman scattering
SFM. *See* Scanning force microscope
Silicon
  chemical etching 283–293
  HF treatment 305–313
  oxide formation 284–286
  oxide removal 286–287
  porous
    confocal imaging 295–304
    formation 287–289
  Si/SiGe epitaxy 347–356
Silicon(111), oxygen adsorption 315–324
Silicon dioxide/silicon interface 43–44
Silicon germanium, epitaxy on Si 347–356
Silicon/chlorine systems 136–138
Silver films 187–195
Silver/CH_3 109–110, 114–116, 121–126
Silver/COOH 109–110, 114–116, 121–126
SIMS. *See* Secondary ion mass spectrometry
Spin splitting, image states 151–154
12-(9-anthroyloxy) Stearic acid (12-AS) 243–245
STM. *See* Scanning tunneling microscopy
Stranski-Krastonov growth 161–163
Sulfate ion, copper electrocrystallization 233–235
Sulfur passivated InP(100) 325–334, 337–341
Sulfur/rhenium
  coadsorbate-induced compression 23
  structures 5–8
Superlattices, Tamm surfaces states 65–76
Surface Charge Spectroscopy (SCS) 357–376
  accuracy of D_{it} measurements 374
  back content 371
  charge traps 364–369
  dielectric breakdown measurements 373–374
  dielectric layer thickness 373
  dielectric surface potential 372–373
  instrumentation 370–371
  interface traps 359–363
  surface band bending 372–373
Surface cleaning, *in situ* 347–356
Surface defects 27
Surface electronic structure 81–85
Surface Enhanced Raman Scattering (SERS) 55–64
  silver films 187–195
  simulation 62–64
Surface Ion Neutralization, Laser-Assisted 389–405
Surfactants, insoluble 237–246
Synchroton-based techniques 37–40

Tamm surfaces states, semiconductor superlattices 65–76
Temperature-dependence, adatom vibrations 220–221
Tensor LEED analyses 247–257
Terminated Kronig-Penney-type model 66–67
Theory of Light in Complex Structures 57–60
Ti6A14V, surface preparation 269–279
Titanium, surface preparation 269–279
Titanium dioxide, surface geometry 80–81
TMP. *See* Transient microwave photoconductivity

Transient microwave photoconductivity (TMP), Advanced Method 305–313
Transmission electron microscope 350–353
Two-dimensional electron systems, magnetic fields 91–101
Two-phonon emission, adatom vibration 221–225

UV-Photon Radiation, photochemical desorption 141–143

Vibrational line shape, adatoms 217–225
Vibrational spectroscopy 173–185
    Low-Energy Electron Diffraction 9–10

Water, at surfaces 173–185
Wave function, superlattice surface states 68–69
Weak interactions, metal/organic functional groups 103–129

X-ray absorption near-edge structure (XANES), semiconductor passivation 335–345
X-ray photoelectron spectroscopy (XPS)
    Ag/CH_3 114–116
    Ag/COOH 114–116
    Cu/CN 116–119
    Cu/OH 119–121
    oxygen adsorption on silicon(111) 315–324
    SAMs 111–112
    sulfur passivated InP(100) 331–333
    Ti6A14V surface preparation 269–279
    Ti surface preparation 269–279
    zinc phosphate coating process 259–267
XANES. *See* X-ray absorption near-edge structure
XPS. *See* X-ray photoelectron spectroscopy

Zinc oxide, zinc phosphate coating process 265–266
Zinc phosphate, 7075-T6 aluminum alloy 259–267

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